

HIGH VOLTEGE DIODE

ESJC35 is high reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

Features

- Low V_F
- High reliability .
- High speed switching

Applications

- Rectification for X-ray generator high voltage power supply

Maximum Ratings and Characteristics

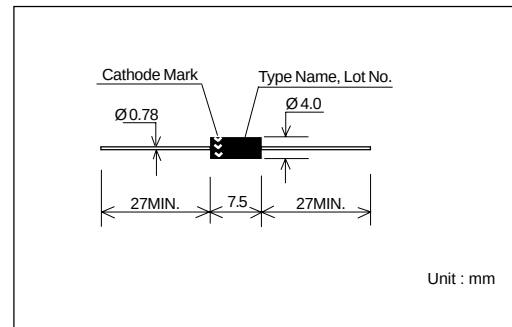
- Absolute Maximum Ratings

Items	Symbols	Conditions	ESJC35-08	Units
Repetitive Peak Reverse Voltage	V_{RRM}		8.0	kV
Average Forward Current	I_o	$T_{oil}=25^{\circ}C$, Resistive Load	410	mA
Non-repetitive Peak Forward Current	I_{FSM}	50Hz.sine harf-wave peak value. One-shot. $T_a=25^{\circ}C$	10	A
Allowable Junction Temperature	T_j		120	$^{\circ}C$
Storage Temperature Range	T_{stg}		-40 to +120	$^{\circ}C$

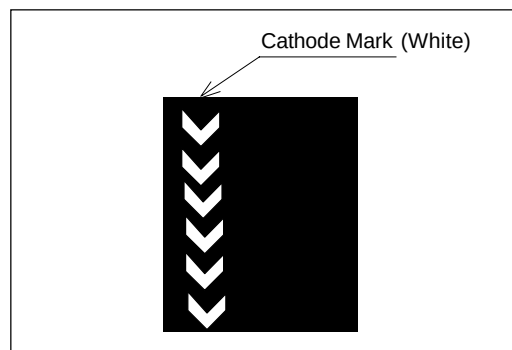
- Electrical Characteristics ($T_a=25^{\circ}C$ Unless otherwise specified)

Items	Symbols	Conditions	ESJC35-08	Units
Maximum Forward Voltage Drop	V_F	at $25^{\circ}C$, $I_F=1A$	20	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$, $V_R=8.0kV$	2	μA
	I_{R2}	at $100^{\circ}C$, $V_R=8.0kV$	10	
Minimum Reverse Recovery Time	t_{rr}	at $25^{\circ}C$, $I_F=I_R=100mA$ 90%Recovery	0.15	μs

Outline Drawings



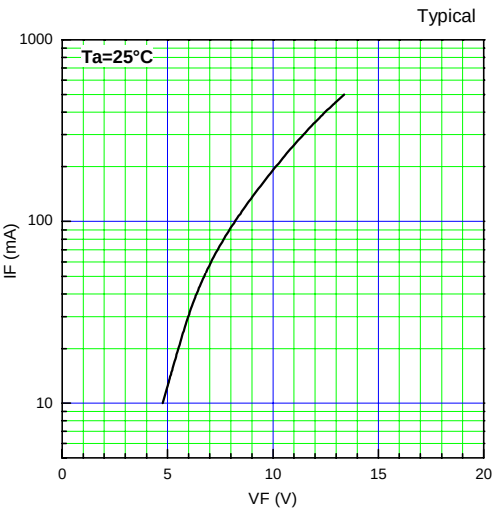
Cathode Mark



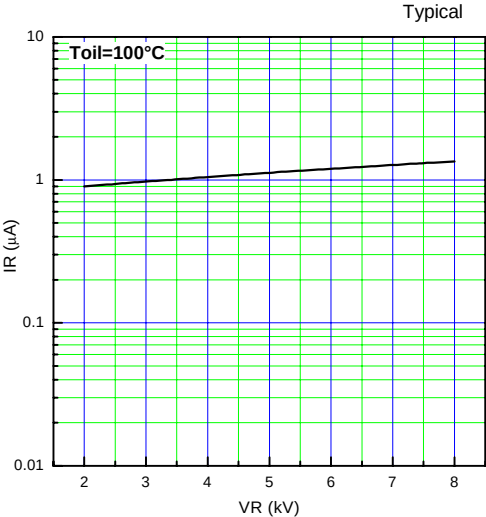
ESJC35 (8.0kV/410mA)

■ Characteristics

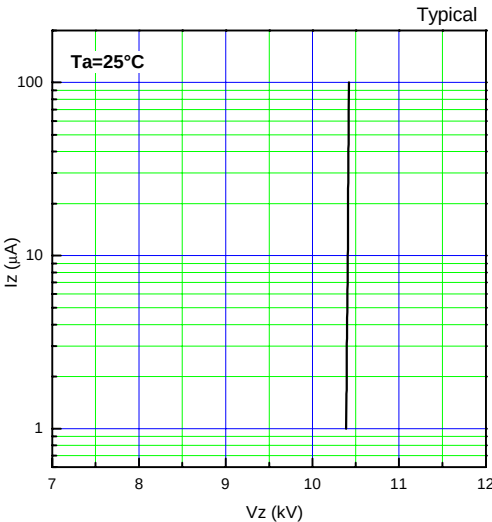
Forward characteristic [VF-IF]



Reverse characteristic [VR-IR]



Avalanche characteristic [Vz-Iz]



Reverse recovery time characteristic [Ta-trr]

